

L Number	Hits	Search Text	DB	Time stamp
1	10	438/525.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 10:11
-	2124	(field adj effect adj transistor) and (ion adj implant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:39
-	6	438/525.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 10:10
-	85	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:01
-	34	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 18:56
-	34	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 13:44
-	5	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (lithography)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 18:59
-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (pocket adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:00
-	4	438/197.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:02
-	27	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:04
-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask) and (conductive adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:05
-	5	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask) and (conductive adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:05
-	6	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask) and (conduct\$3 adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:06
-	18	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 15:51
-	12	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask with spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 16:05
-	1	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask with dielectric adj spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 15:57

-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (taper with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 16:07
-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (taper\$2 with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 16:11
-	5	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (reduced with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 16:12
-	0	EP-1263027-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:41
-	2	EP-1263027-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:04
-	12213048	US 5731239.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:54
-	2	5731239.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:57
-	4	512063.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:58
-	2	5120637.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:58
-	2	5120673.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:10
-	0	JP-88317951-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:23
-	0	JP-2162738-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:06
-	0	JP-2162738 A-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:07
-	2	5021355.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:13
-	2	6501133.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:15
-	0	2020050621.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:25
-	0	2000648044.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:17
-	2	20020050621.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:18

-	2	5731239.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:19
-	2	5120673.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:19
-	1	JP-56048174-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:23
-	2	5021355.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:25